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Kind regards,

Team Nexperia



PNP resistor-equipped transistor; R1 = 100 kΩ, R2 = 100 kΩRev. 1 — 1 June 2012Product data at a

Product data sheet

#### **Product profile** 1.

#### **1.1 General description**

PNP Resistor-Equipped Transistor (RET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

NPN complement: PDTC115EMB.

#### 1.2 Features and benefits

- 20 mA output current capability
- Reduces component count
- Built-in bias resistors
- Reduces pick and place costs

### **1.3 Applications**

- Low-current peripheral driver
- Control of IC inputs

- Simplifies circuit design
- AEC-Q101 gualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Replaces general-purpose transistors in digital applications
- Mobile applications

#### 1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-50	V
lo	output current		-	-	-20	mA
R1	bias resistor 1 (input)	T <sub>amb</sub> = 25 °C	70	100	130	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



PNP resistor-equipped transistor; R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$ 

# 2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)		
2	G	GND (emitter)		3
3	0	output (collector)	2 Transparent top view SOT883B (DFN1006B-3)	1 R1 R2 2 sym003

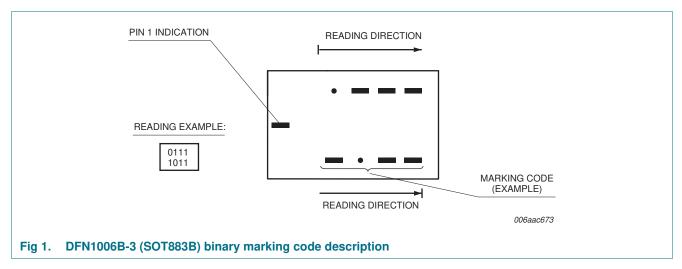
# 3. Ordering information

Table 3. Ordering information							
Type number Package							
	Name	Description	Version				
PDTA115EMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B				

# 4. Marking

Table 4.	Marking	codes
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Type number	Marking code
PDTA115EMB	0010 0000



PNP resistor-equipped transistor; R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$ 

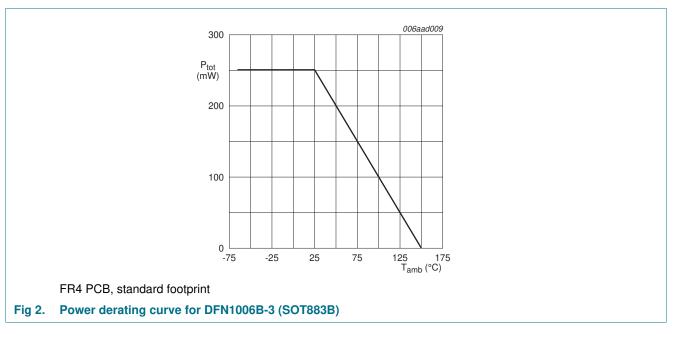
### 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-10	V
VI	input voltage	positive		-	10	V
		negative		-	-40	V
lo	output current			-	-20	mA
I <sub>CM</sub>	peak collector current	pulsed; t <sub>p</sub> ≤ 1 ms		-	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	<u>[1]</u>	-	250	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



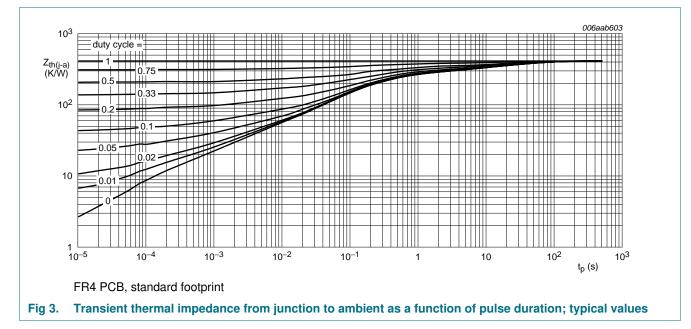
### 6. Thermal characteristics

Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

# PDTA115EMB

PNP resistor-equipped transistor; R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$ 



## 7. Characteristics

#### Table 7. Characteristics

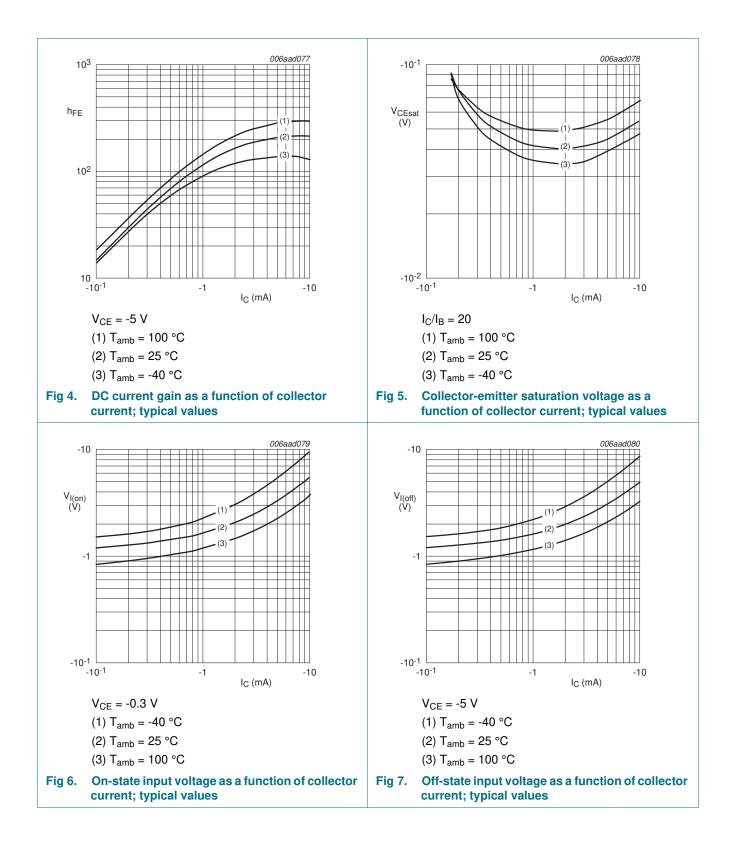
Table 7.	Characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB}$ = -50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off	$V_{CE}$ = -30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	-1	μA
	current	$V_{CE}$ = -30 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	-5	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = -5 V; $I_C$ = 0 A; $T_{amb}$ = 25 °C		-	-	-50	μA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -5 V; $I_{C}$ = -5 mA; $T_{amb}$ = 25 °C		80	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C}$ = -5 mA; $I_{B}$ = -0.25 mA; $T_{amb}$ = 25 °C		-	-	-150	mV
V <sub>I(off)</sub>	off-state input voltage	$V_{CE} = -5 \text{ V};  I_C = -100  \mu\text{A};  T_{amb} = 25 ^\circ\text{C}$		-	-1.2	-0.5	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE}$ = -0.3 V; I <sub>C</sub> = -1 mA; T <sub>amb</sub> = 25 °C		-3	-1.6	-	V
R1	bias resistor 1 (input)	$T_{amb} = 25 \ ^{\circ}C$		70	100	130	kΩ
R2/R1	bias resistor ratio			0.8	1	1.2	
C <sub>C</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C		-	-	3	pF
f <sub>T</sub>	transition frequency	$\label{eq:Vce} \begin{array}{l} V_{CE} = -5 \ V; \ I_C = -10 \ m\text{A}; \ f = 100 \ \text{MHz}; \\ T_{amb} = 25 \ ^{\circ}\text{C} \end{array}$	[1]	-	180	-	MHz

[1] Characteristics of built-in transistor.

PDTA115EMB Product data sheet

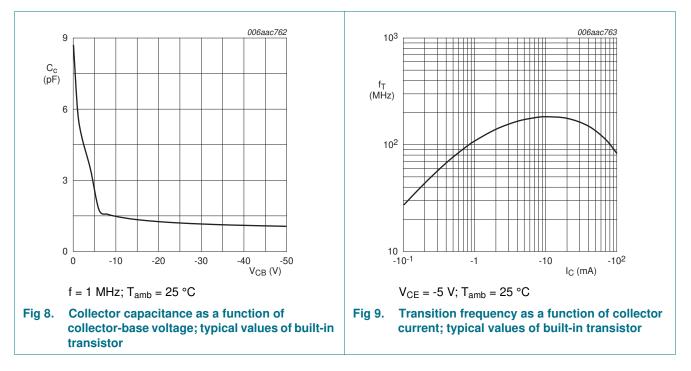
# PDTA115EMB

#### PNP resistor-equipped transistor; R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$



#### **NXP Semiconductors**

PNP resistor-equipped transistor; R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$ 



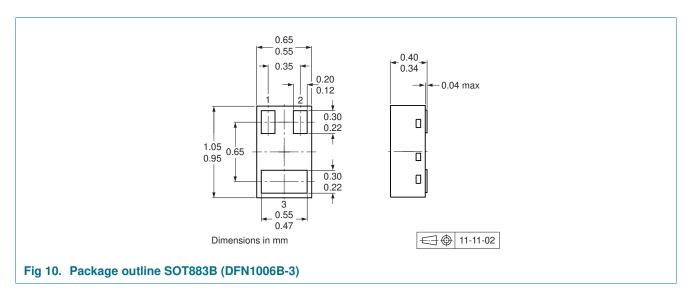
### 8. Test information

#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

PNP resistor-equipped transistor; R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$ 

#### **Package outline** 9.



### 10. Soldering

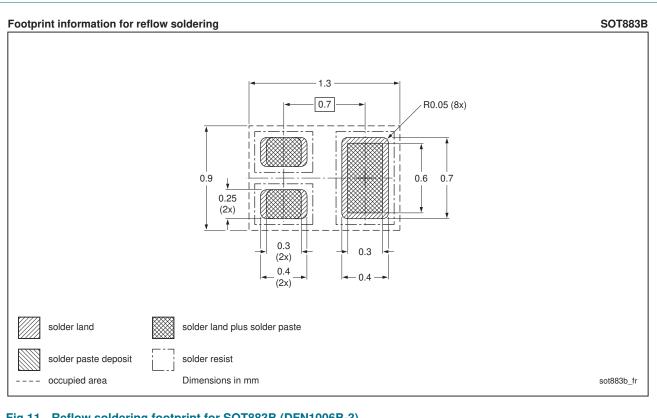


Fig 11. Reflow soldering footprint for SOT883B (DFN1006B-3)

PDTA115EMB **Product data sheet** 

PNP resistor-equipped transistor; R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$ 

# 11. Revision history

Table 8. Revision	Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
PDTA115EMB v.1	20120601	Product data sheet	-	-			

PNP resistor-equipped transistor; R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$ 

### 12. Legal information

#### 12.1 Data sheet status

Document status <sup>[1]</sup> <sup>[2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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**Product data sheet** 

PDTA115EMB

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# PDTA115EMB

PNP resistor-equipped transistor; R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$ 

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